

-	182	((amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 11:33
-	140	amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:42
-	0	amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved))	USPAT	2003/06/18 14:05
-	10	amorphizing amorphization amorphized amorphous) with (ion implant implantation implanting implanted) and ((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (((amorphizing amorphization amorphized) and (438/6 257/\$6)) and (recrystal crystal crystallize crystallization crystallizing recrystallize recrystallization recrystallizing anneal annealing annealling annealed) with (amorphized amorphous))) not (((amorphizing amorphization amorphized) with (trench groove recess recessed grooved))	USPAT	2003/06/18 14:05
-	554	trench with DRAM with isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:45
-	7	(trench with DRAM with isolation) and conformal near (insulator oxide dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:43
-	4	(trench with DRAM with isolation) and conformal near (insulator oxide dioxide) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:44
-	170	trench with DRAM with sti	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:45
-	8	trench with DRAM near2 sti	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:46
-	53	trench with DRAM near4 sti not (trench with DRAM near2 sti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:47
-	18	trench with DRAM and conformal near2 (silicon near oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:48

-	6	trench with DRAM and conformal near2 (silicon near oxide) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/18 15:48
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